

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS™ P6

600V CoolMOS™ P6 Power Transistor  
IPx60R330P6

## Data Sheet

Rev. 2.2  
Final

## 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ P6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter and cooler.

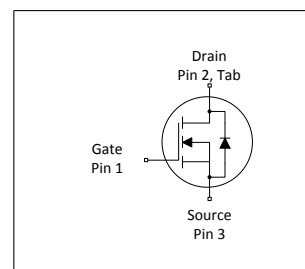
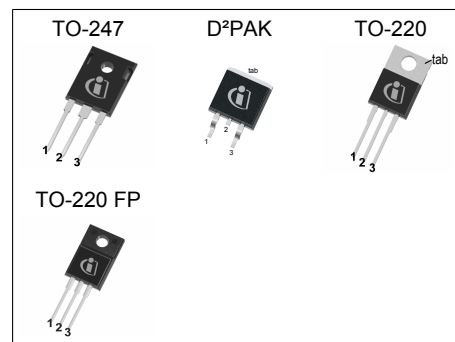
## Features

- Increased MOSFET dv/dt ruggedness
- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)

## Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*



**Table 1 Key Performance Parameters**

| Parameter            | Value | Unit |
|----------------------|-------|------|
| $V_{DS} @ T_{j,max}$ | 650   | V    |
| $R_{DS(on),max}$     | 330   | mΩ   |
| $Q_{g,typ}$          | 22    | nC   |
| $I_{D,pulse}$        | 33    | A    |
| $E_{oss@400V}$       | 3     | μJ   |
| Body diode di/dt     | 500   | A/μs |

| Type / Ordering Code | Package           | Marking | Related Links  |
|----------------------|-------------------|---------|----------------|
| IPW60R330P6          | PG-TO 247         | 6R330P6 | see Appendix A |
| IPB60R330P6          | PG-TO 263         |         |                |
| IPP60R330P6          | PG-TO 220         |         |                |
| IPA60R330P6          | PG-TO 220 FullPAK |         |                |

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## 2 Maximum ratings

at  $T_j = 25^\circ\text{C}$ , unless otherwise specified

**Table 2 Maximum ratings**

| Parameter                                                 | Symbol        | Values |      |             | Unit             | Note / Test Condition                                                                  |
|-----------------------------------------------------------|---------------|--------|------|-------------|------------------|----------------------------------------------------------------------------------------|
|                                                           |               | Min.   | Typ. | Max.        |                  |                                                                                        |
| Continuous drain current <sup>1)</sup>                    | $I_D$         | -      | -    | 12.0<br>7.6 | A                | $T_C=25^\circ\text{C}$<br>$T_C=100^\circ\text{C}$                                      |
| Pulsed drain current <sup>2)</sup>                        | $I_{D,pulse}$ | -      | -    | 33          | A                | $T_C=25^\circ\text{C}$                                                                 |
| Avalanche energy, single pulse                            | $E_{AS}$      | -      | -    | 247         | mJ               | $I_D=2.1\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 12                                 |
| Avalanche energy, repetitive                              | $E_{AR}$      | -      | -    | 0.37        | mJ               | $I_D=2.1\text{A}$ ; $V_{DD}=50\text{V}$ ; see table 12                                 |
| Avalanche current, repetitive                             | $I_{AR}$      | -      | -    | 2.1         | A                | -                                                                                      |
| MOSFET dv/dt ruggedness                                   | dv/dt         | -      | -    | 100         | V/ns             | $V_{DS}=0\dots400\text{V}$                                                             |
| Gate source voltage (static)                              | $V_{GS}$      | -20    | -    | 20          | V                | static;                                                                                |
| Gate source voltage (dynamic)                             | $V_{GS}$      | -30    | -    | 30          | V                | AC ( $f>1\text{ Hz}$ )                                                                 |
| Power dissipation (Non FullPAK)<br>TO-220, TO-263, TO-247 | $P_{tot}$     | -      | -    | 93          | W                | $T_C=25^\circ\text{C}$                                                                 |
| Power dissipation (FullPAK)<br>TO-220FP                   | $P_{tot}$     | -      | -    | 32          | W                | $T_C=25^\circ\text{C}$                                                                 |
| Storage temperature                                       | $T_{stg}$     | -55    | -    | 150         | $^\circ\text{C}$ | -                                                                                      |
| Operating junction temperature                            | $T_j$         | -55    | -    | 150         | $^\circ\text{C}$ | -                                                                                      |
| Mounting torque (Non FullPAK)<br>TO-220, TO-247           | -             | -      | -    | 60          | Ncm              | M3 and M3.5 screws                                                                     |
| Mounting torque (FullPAK)<br>TO-220FP                     | -             | -      | -    | 50          | Ncm              | M2.5 screws                                                                            |
| Continuous diode forward current                          | $I_S$         | -      | -    | 10.4        | A                | $T_C=25^\circ\text{C}$                                                                 |
| Diode pulse current <sup>2)</sup>                         | $I_{S,pulse}$ | -      | -    | 33          | A                | $T_C=25^\circ\text{C}$                                                                 |
| Reverse diode dv/dt <sup>3)</sup>                         | dv/dt         | -      | -    | 15          | V/ns             | $V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq I_S$ , $T_j=25^\circ\text{C}$<br>see table 10 |
| Maximum diode commutation speed                           | di/dt         | -      | -    | 500         | A/ $\mu\text{s}$ | $V_{DS}=0\dots400\text{V}$ , $I_{SD}\leq I_S$ , $T_j=25^\circ\text{C}$<br>see table 10 |
| Insulation withstand voltage for<br>TO-220FP              | $V_{ISO}$     | -      | -    | 2500        | V                | $V_{rms}$ , $T_C=25^\circ\text{C}$ , $t=1\text{min}$                                   |

<sup>1)</sup> Limited by  $T_{j,max}$ . Maximum duty cycle  $D=0.75$

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Identical low side and high side switch with identical  $R_G$

### 3 Thermal characteristics

**Table 3 Thermal characteristics (Non FullPAK) TO-220, TO-247**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition               |
|------------------------------------------------------------|------------|--------|------|------|------|-------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                     |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 1.35 | °C/W | -                                   |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 62   | °C/W | leaded                              |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6mm (0.063 in.) from case for 10s |

**Table 4 Thermal characteristics (FullPAK) TO-220FP**

| Parameter                                                  | Symbol     | Values |      |      | Unit | Note / Test Condition               |
|------------------------------------------------------------|------------|--------|------|------|------|-------------------------------------|
|                                                            |            | Min.   | Typ. | Max. |      |                                     |
| Thermal resistance, junction - case                        | $R_{thJC}$ | -      | -    | 3.95 | °C/W | -                                   |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | -      | -    | 80   | °C/W | leaded                              |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | -      | -    | 260  | °C   | 1.6mm (0.063 in.) from case for 10s |

**Table 5 Thermal characteristics TO-263**

| Parameter                                              | Symbol     | Values |      |      | Unit | Note / Test Condition                                                                                                                                                   |
|--------------------------------------------------------|------------|--------|------|------|------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|                                                        |            | Min.   | Typ. | Max. |      |                                                                                                                                                                         |
| Thermal resistance, junction - case                    | $R_{thJC}$ | -      | -    | 1.35 | °C/W | -                                                                                                                                                                       |
| Thermal resistance, junction - ambient                 | $R_{thJA}$ | -      | -    | 62   | °C/W | device on PCB, minimal footprint                                                                                                                                        |
| Thermal resistance, junction - ambient for SMD version | $R_{thJA}$ | -      | 35   | 45   | °C/W | Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling. |
| Soldering temperature, wave & reflow soldering allowed | $T_{sold}$ | -      | -    | 260  | °C   | reflow MSL1                                                                                                                                                             |

## 4 Electrical characteristics

at  $T_j=25^\circ\text{C}$ , unless otherwise specified

**Table 6 Static characteristics**

| Parameter                        | Symbol        | Values |                |            | Unit     | Note / Test Condition                                                                                       |
|----------------------------------|---------------|--------|----------------|------------|----------|-------------------------------------------------------------------------------------------------------------|
|                                  |               | Min.   | Typ.           | Max.       |          |                                                                                                             |
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | 600    | -              | -          | V        | $V_{GS}=0V$ , $I_D=1mA$                                                                                     |
| Gate threshold voltage           | $V_{(GS)th}$  | 3.5    | 4.0            | 4.5        | V        | $V_{DS}=V_{GS}$ , $I_D=0.37mA$                                                                              |
| Zero gate voltage drain current  | $I_{DSS}$     | -      | -              | 1          | $\mu A$  | $V_{DS}=600$ , $V_{GS}=0V$ , $T_j=25^\circ\text{C}$<br>$V_{DS}=600$ , $V_{GS}=0V$ , $T_j=150^\circ\text{C}$ |
| Gate-source leakage current      | $I_{GSS}$     | -      | -              | 100        | nA       | $V_{GS}=20V$ , $V_{DS}=0V$                                                                                  |
| Drain-source on-state resistance | $R_{DS(on)}$  | -      | 0.297<br>0.772 | 0.330<br>- | $\Omega$ | $V_{GS}=10V$ , $I_D=4.5A$ , $T_j=25^\circ\text{C}$<br>$V_{GS}=10V$ , $I_D=4.5A$ , $T_j=150^\circ\text{C}$   |
| Gate resistance                  | $R_G$         | -      | 6.7            | -          | $\Omega$ | $f=1MHz$ , open drain                                                                                       |

**Table 7 Dynamic characteristics**

| Parameter                                                  | Symbol       | Values |      |      | Unit | Note / Test Condition                                                         |
|------------------------------------------------------------|--------------|--------|------|------|------|-------------------------------------------------------------------------------|
|                                                            |              | Min.   | Typ. | Max. |      |                                                                               |
| Input capacitance                                          | $C_{iss}$    | -      | 1010 | -    | pF   | $V_{GS}=0V$ , $V_{DS}=100V$ , $f=1MHz$                                        |
| Output capacitance                                         | $C_{oss}$    | -      | 47   | -    | pF   | $V_{GS}=0V$ , $V_{DS}=100V$ , $f=1MHz$                                        |
| Effective output capacitance, energy related <sup>1)</sup> | $C_{o(er)}$  | -      | 38   | -    | pF   | $V_{GS}=0V$ , $V_{DS}=0...400V$                                               |
| Effective output capacitance, time related <sup>2)</sup>   | $C_{o(tr)}$  | -      | 155  | -    | pF   | $I_D=\text{constant}$ , $V_{GS}=0V$ , $V_{DS}=0...400V$                       |
| Turn-on delay time                                         | $t_{d(on)}$  | -      | 12   | -    | ns   | $V_{DD}=400V$ , $V_{GS}=13V$ , $I_D=5.6A$ ,<br>$R_G=3.4\Omega$ ; see table 11 |
| Rise time                                                  | $t_r$        | -      | 7    | -    | ns   | $V_{DD}=400V$ , $V_{GS}=13V$ , $I_D=5.6A$ ,<br>$R_G=3.4\Omega$ ; see table 11 |
| Turn-off delay time                                        | $t_{d(off)}$ | -      | 33   | -    | ns   | $V_{DD}=400V$ , $V_{GS}=13V$ , $I_D=5.6A$ ,<br>$R_G=3.4\Omega$ ; see table 11 |
| Fall time                                                  | $t_f$        | -      | 7    | -    | ns   | $V_{DD}=400V$ , $V_{GS}=13V$ , $I_D=5.6A$ ,<br>$R_G=3.4\Omega$ ; see table 11 |

**Table 8 Gate charge characteristics**

| Parameter             | Symbol        | Values |      |      | Unit | Note / Test Condition                            |
|-----------------------|---------------|--------|------|------|------|--------------------------------------------------|
|                       |               | Min.   | Typ. | Max. |      |                                                  |
| Gate to source charge | $Q_{gs}$      | -      | 6    | -    | nC   | $V_{DD}=400V$ , $I_D=5.6A$ , $V_{GS}=0$ to $10V$ |
| Gate to drain charge  | $Q_{gd}$      | -      | 8    | -    | nC   | $V_{DD}=400V$ , $I_D=5.6A$ , $V_{GS}=0$ to $10V$ |
| Gate charge total     | $Q_g$         | -      | 22   | -    | nC   | $V_{DD}=400V$ , $I_D=5.6A$ , $V_{GS}=0$ to $10V$ |
| Gate plateau voltage  | $V_{plateau}$ | -      | 6.1  | -    | V    | $V_{DD}=400V$ , $I_D=5.6A$ , $V_{GS}=0$ to $10V$ |

<sup>1)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

<sup>2)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 400V

**Table 9 Reverse diode characteristics**

| Parameter                     | Symbol    | Values |      |      | Unit    | Note / Test Condition                                         |
|-------------------------------|-----------|--------|------|------|---------|---------------------------------------------------------------|
|                               |           | Min.   | Typ. | Max. |         |                                                               |
| Diode forward voltage         | $V_{SD}$  | -      | 0.9  | -    | V       | $V_{GS}=0V$ , $I_F=5.6A$ , $T_j=25^{\circ}C$                  |
| Reverse recovery time         | $t_{rr}$  | -      | 257  | -    | ns      | $V_R=400V$ , $I_F=5.6A$ , $di_F/dt=100A/\mu s$ ; see table 10 |
| Reverse recovery charge       | $Q_{rr}$  | -      | 3    | -    | $\mu C$ | $V_R=400V$ , $I_F=5.6A$ , $di_F/dt=100A/\mu s$ ; see table 10 |
| Peak reverse recovery current | $I_{rrm}$ | -      | 18   | -    | A       | $V_R=400V$ , $I_F=5.6A$ , $di_F/dt=100A/\mu s$ ; see table 10 |

## 5 Electrical characteristics diagrams

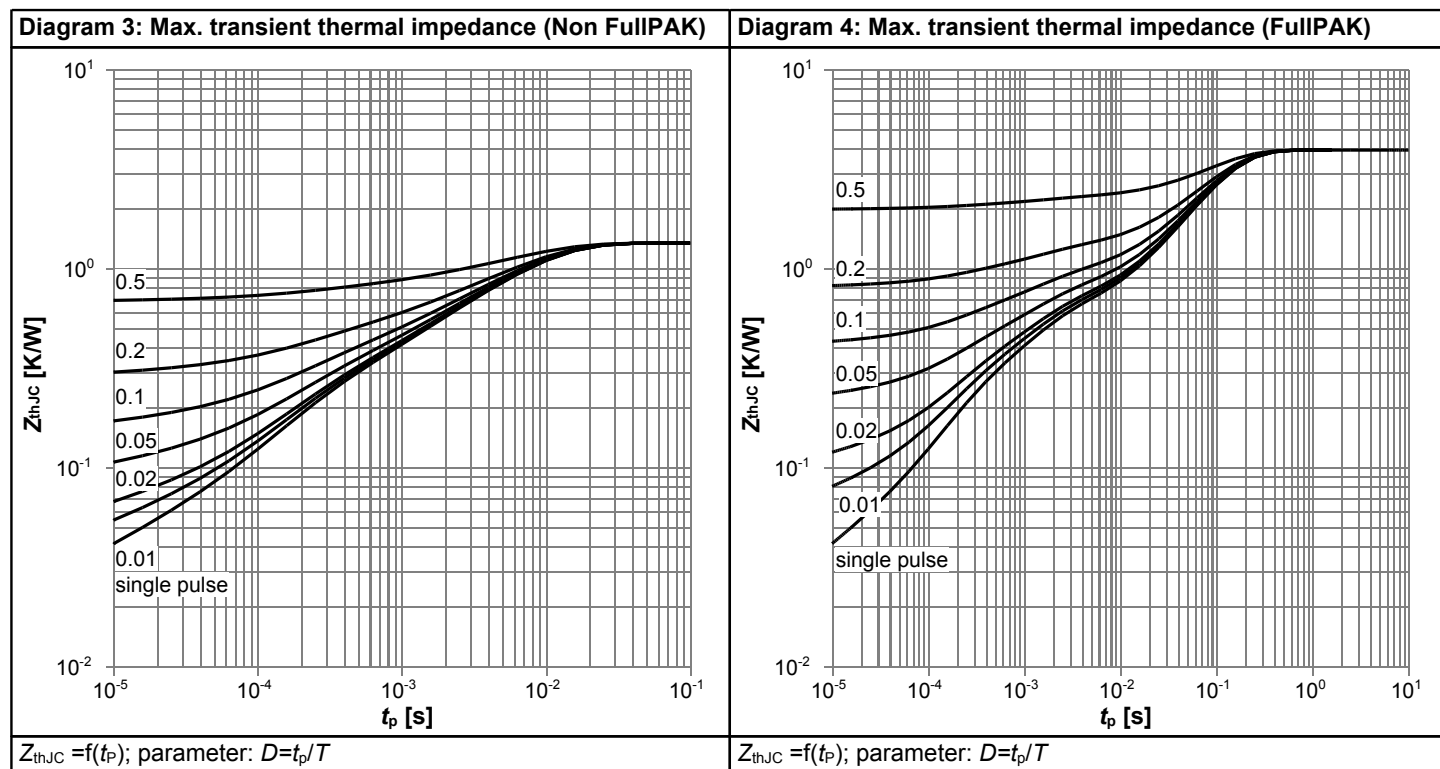
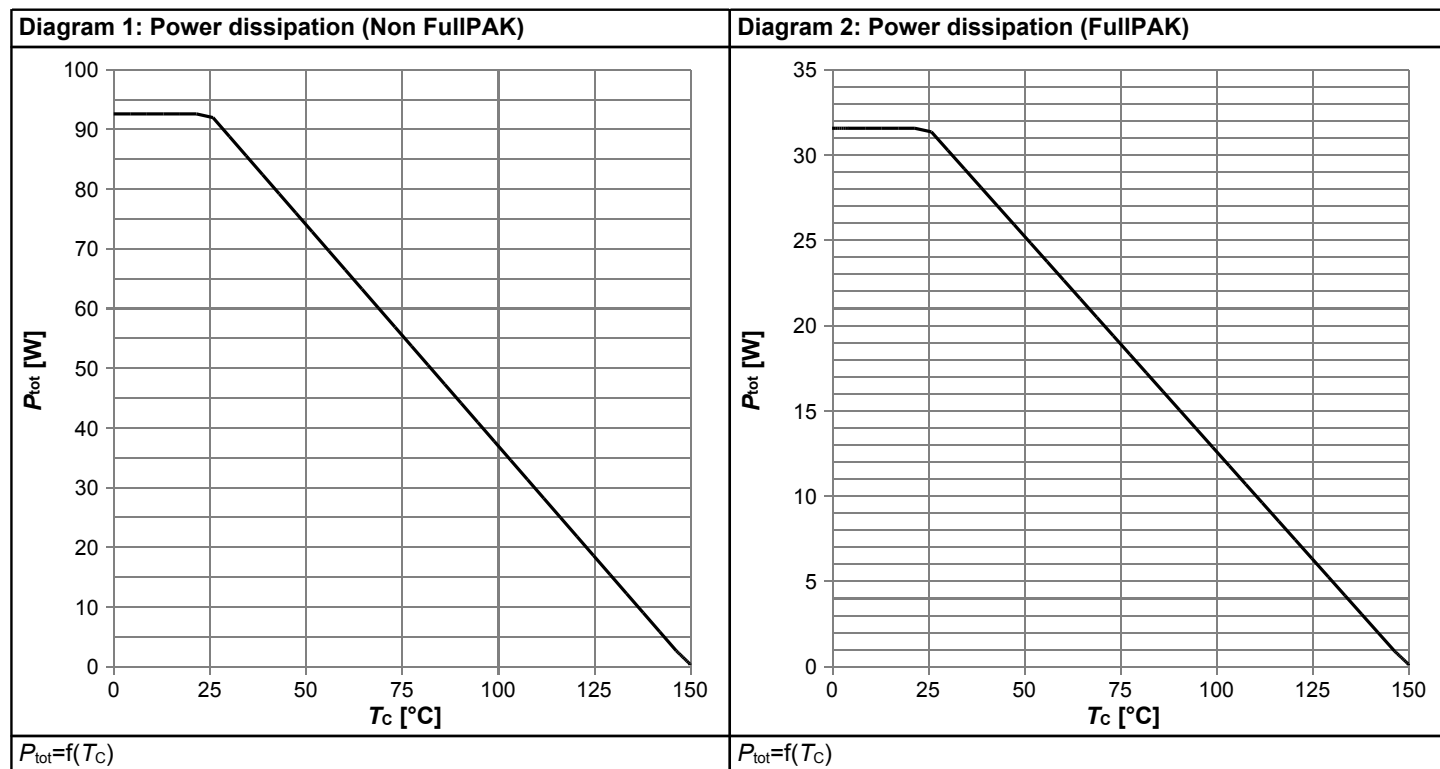
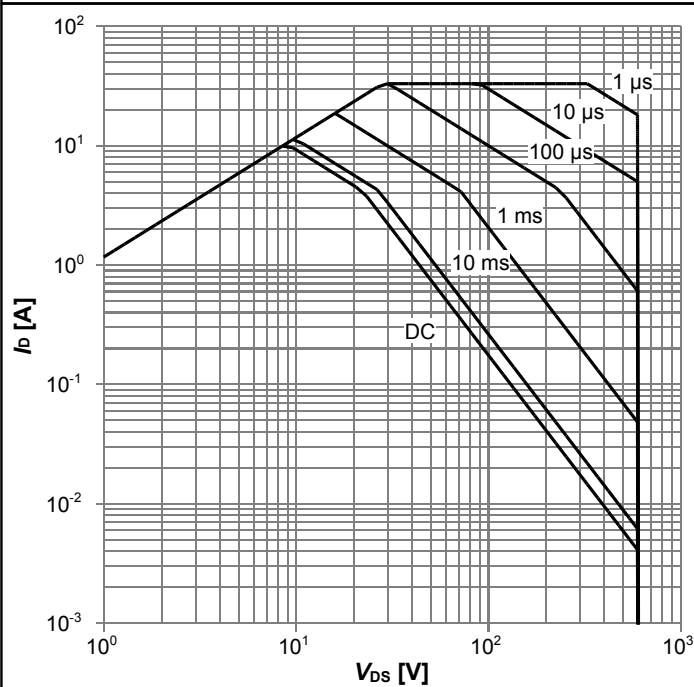
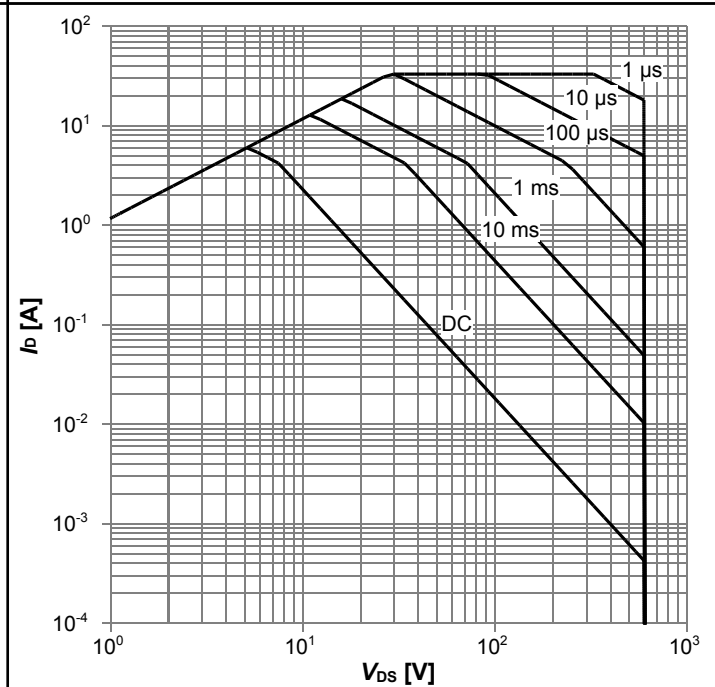


Diagram 5: Safe operating area (Non FullPAK)



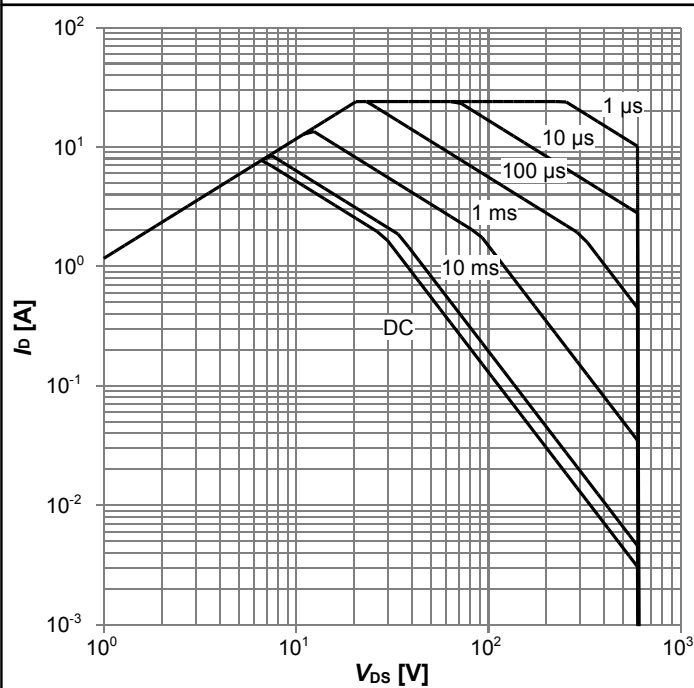
$I_D=f(V_{DS})$ ;  $T_C=25\text{ °C}$ ;  $D=0$ ; parameter:  $t_p$

Diagram 6: Safe operating area (FullPAK)



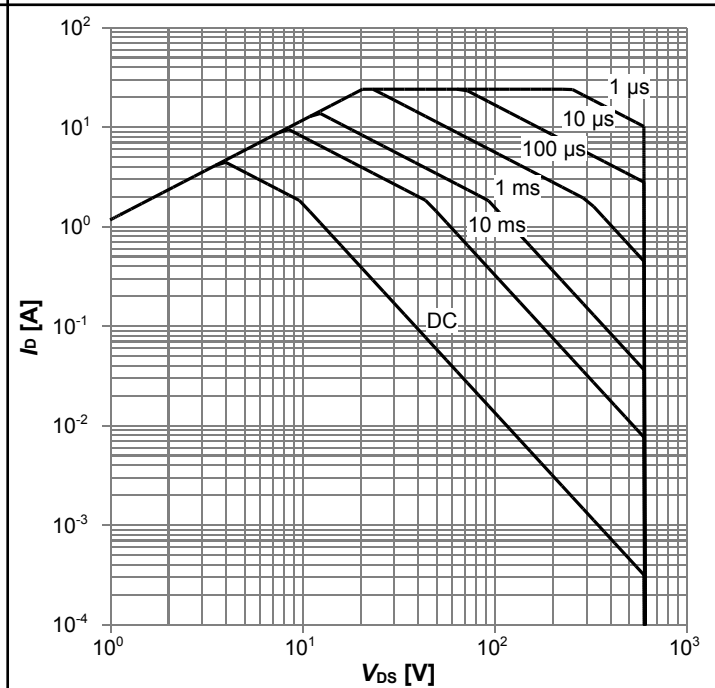
$I_D=f(V_{DS})$ ;  $T_C=25\text{ °C}$ ;  $D=0$ ; parameter:  $t_p$

Diagram 7: Safe operating area (Non FullPAK)



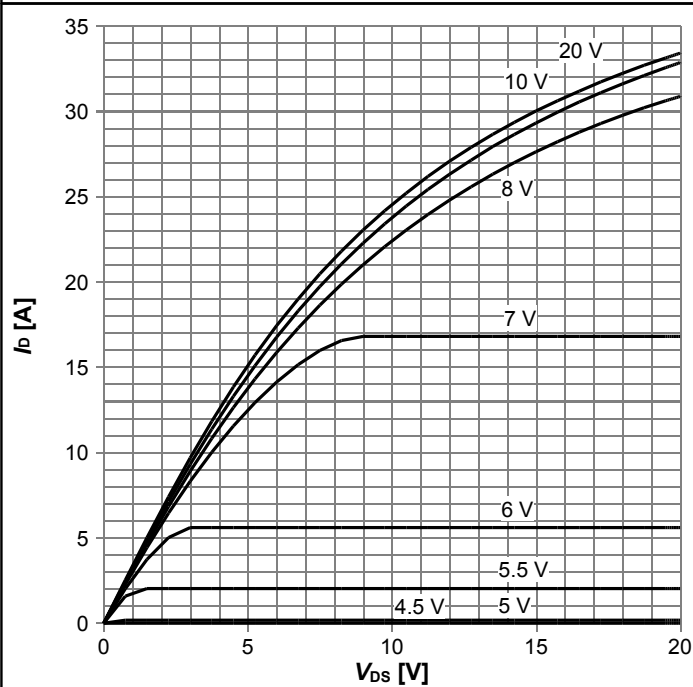
$I_D=f(V_{DS})$ ;  $T_C=80\text{ °C}$ ;  $D=0$ ; parameter:  $t_p$

Diagram 8: Safe operating area (FullPAK)



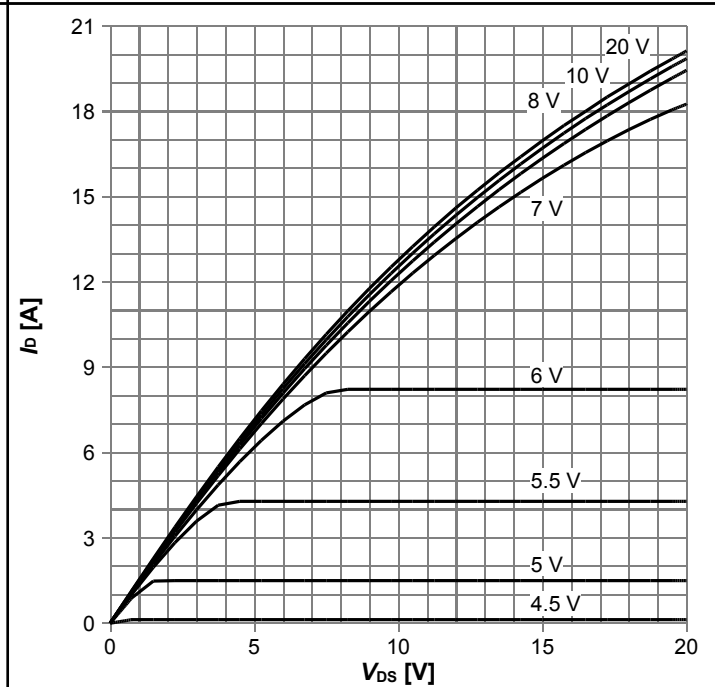
$I_D=f(V_{DS})$ ;  $T_C=80\text{ °C}$ ;  $D=0$ ; parameter:  $t_p$

Diagram 9: Typ. output characteristics



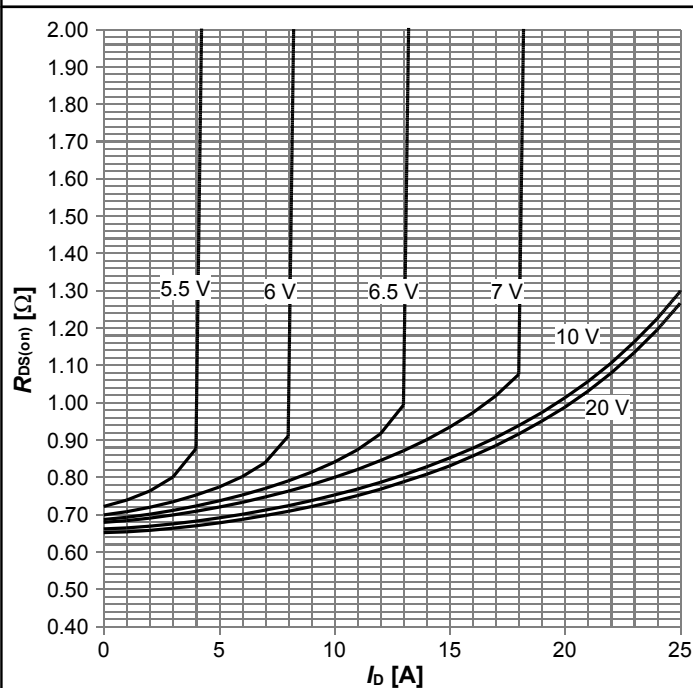
$I_D = f(V_{DS})$ ;  $T_j = 25^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 10: Typ. output characteristics



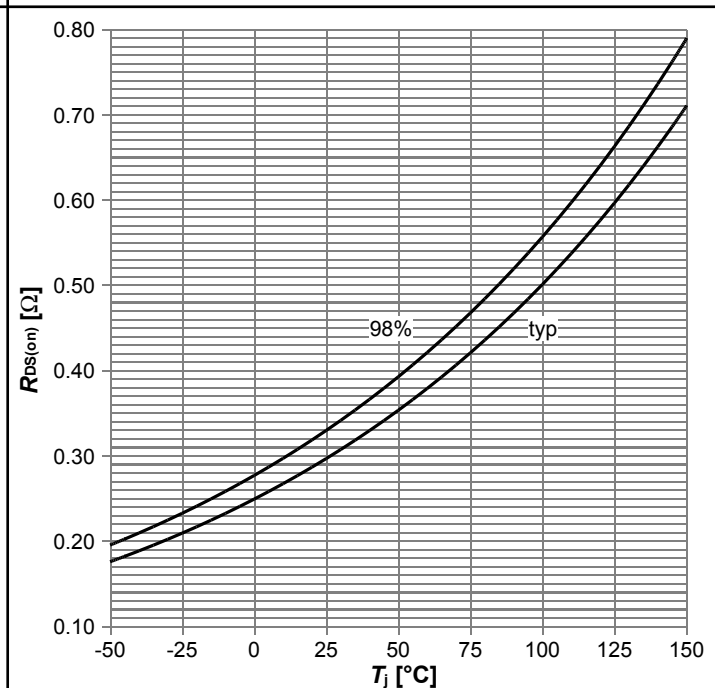
$I_D = f(V_{DS})$ ;  $T_j = 125^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 11: Typ. drain-source on-state resistance



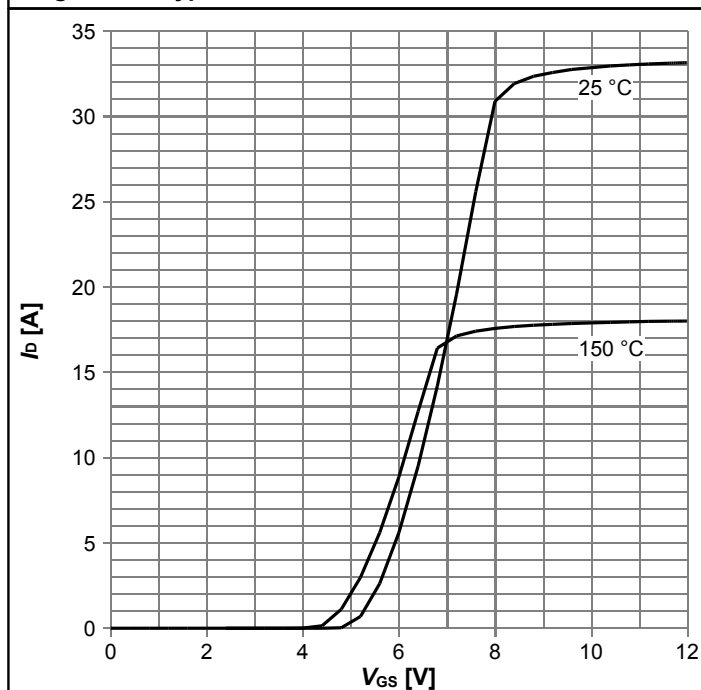
$R_{DS(on)} = f(I_D)$ ;  $T_j = 125^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 12: Drain-source on-state resistance



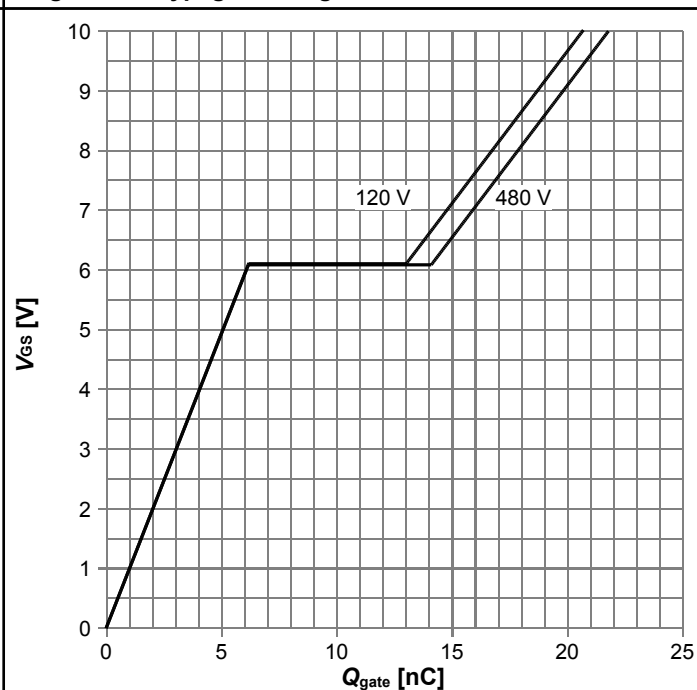
$R_{DS(on)} = f(T_j)$ ;  $I_D = 4.5\text{ A}$ ;  $V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics



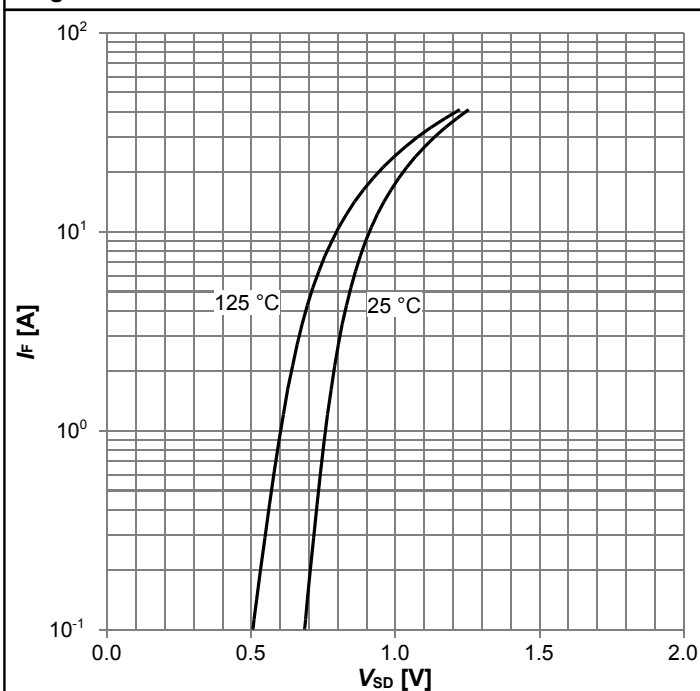
$I_D = f(V_{GS})$ ;  $V_{DS} = 20V$ ; parameter:  $T_j$

Diagram 14: Typ. gate charge



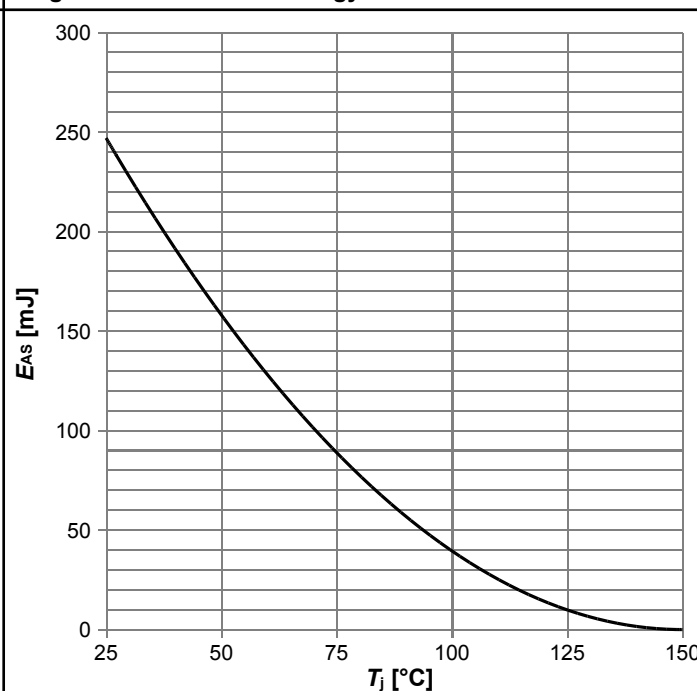
$V_{GS} = f(Q_{gate})$ ;  $I_D = 5.6 A$  pulsed; parameter:  $V_{DD}$

Diagram 15: Forward characteristics of reverse diode



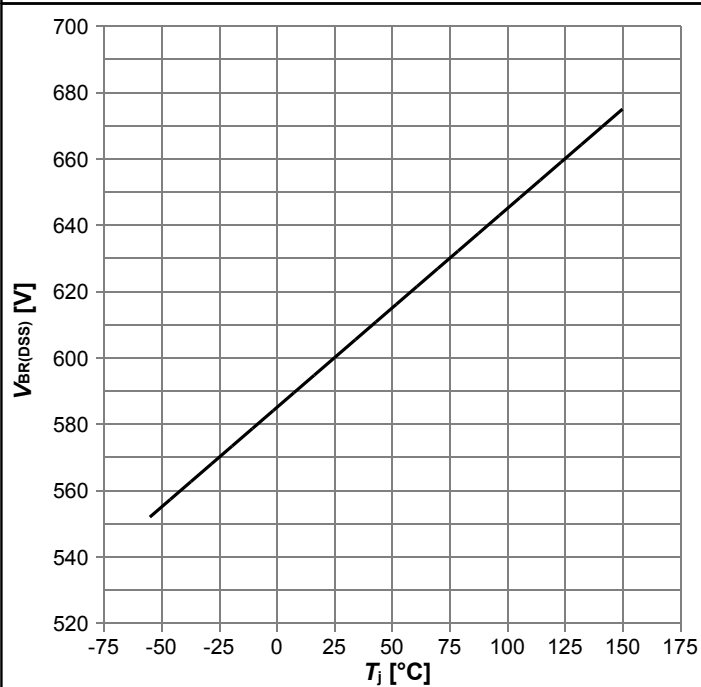
$I_F = f(V_{SD})$ ; parameter:  $T_j$

Diagram 16: Avalanche energy



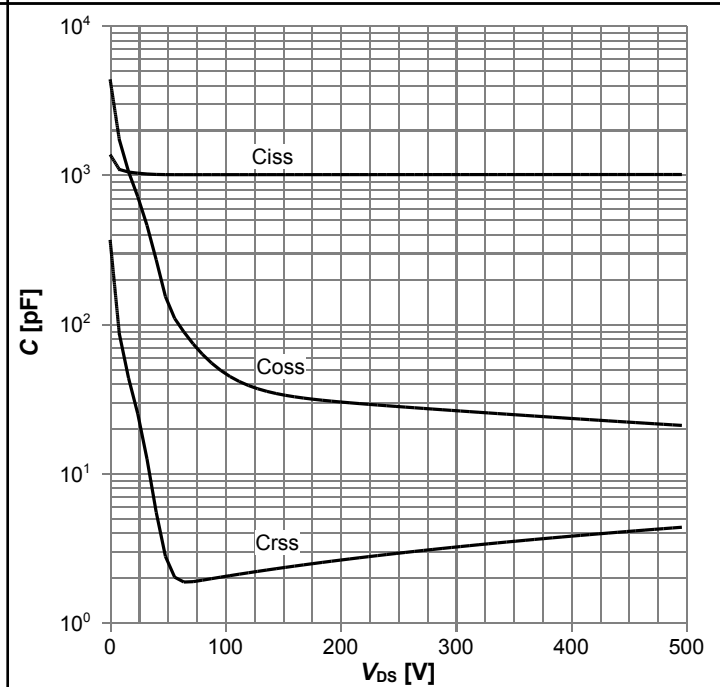
$E_{AS} = f(T_j)$ ;  $I_D = 2.1 A$ ;  $V_{DD} = 50 V$

Diagram 17: Drain-source breakdown voltage



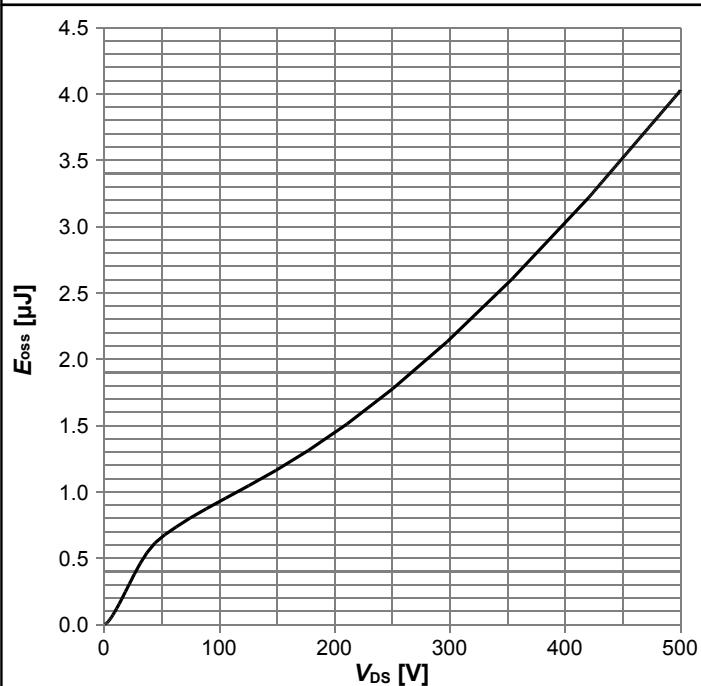
$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$

Diagram 18: Typ. capacitances



$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Diagram 19: Typ. Coss stored energy



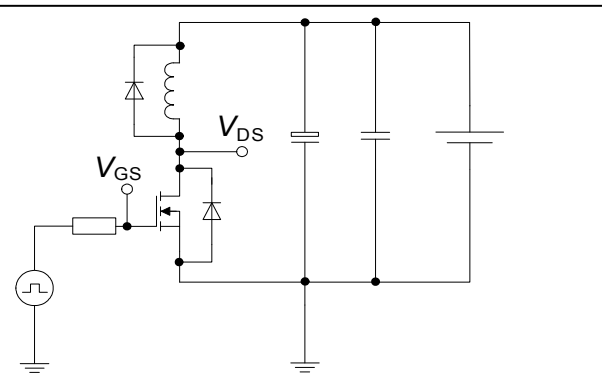
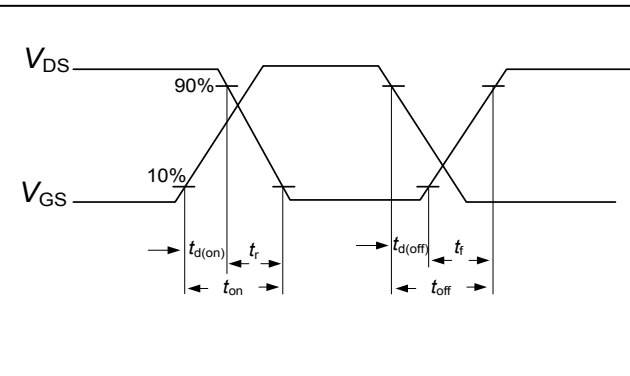
$E_{oss} = f(V_{DS})$

## 6 Test Circuits

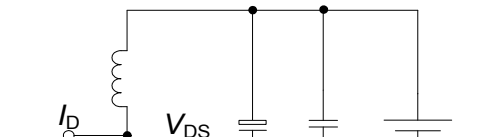
### Table 10 Diode characteristics

|                                                                                   |                                                                                                              |
|-----------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------|
| <p>Test circuit for diode characteristics</p> <p><math>R_{g1} = R_{g2}</math></p> | <p>Diode recovery waveform</p> <p> <math>t_{rr} = t_F + t_S</math><br/> <math>Q_{rr} = Q_F + Q_S</math> </p> |
|-----------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------|

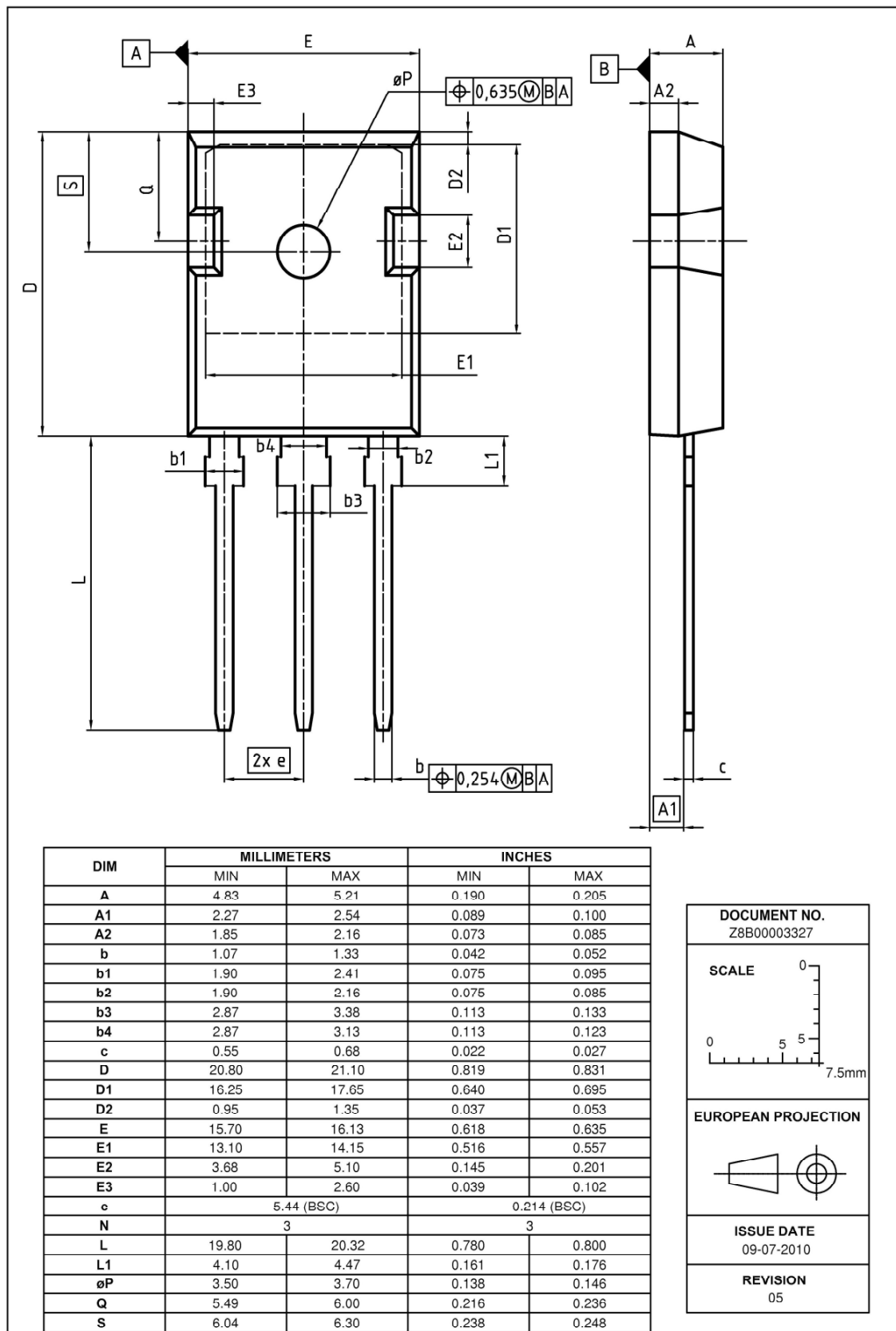
### Table 11 Switching times

| Switching times test circuit for inductive load                                                                                                                                                                                                                                                                                                                                                                                                                                                                           | Switching times waveform                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                                |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
|  <p>The circuit diagram illustrates a switching test setup for an inductive load. A MOSFET is driven by a pulse generator connected to its gate through a resistor. The gate voltage is labeled <math>V_{GS}</math>. The MOSFET's drain is connected to a DC source and an inductive load (represented by an inductor and a diode in parallel). The drain voltage is labeled <math>V_{DS}</math>. The load is connected to ground.</p> |  <p>The waveform diagram shows the switching transitions of the MOSFET. The top trace is the drain-source voltage <math>V_{DS}</math> and the bottom trace is the gate-source voltage <math>V_{GS}</math>. The transitions are marked with vertical lines. The time intervals are labeled as follows:</p> <ul style="list-style-type: none"> <li><math>t_{d(on)}</math>: Delay time from the start of the gate voltage rise to the 90% rise of <math>V_{DS}</math>.</li> <li><math>t_r</math>: Rise time of <math>V_{DS}</math> from 90% to 100%.</li> <li><math>t_{on}</math>: Total turn-on time from the start of the gate voltage rise to the end of the <math>V_{DS}</math> rise.</li> <li><math>t_{d(off)}</math>: Delay time from the start of the gate voltage fall to the 90% fall of <math>V_{DS}</math>.</li> <li><math>t_f</math>: Fall time of <math>V_{DS}</math> from 90% to 100%.</li> <li><math>t_{off}</math>: Total turn-off time from the start of the gate voltage fall to the end of the <math>V_{DS}</math> fall.</li> </ul> |

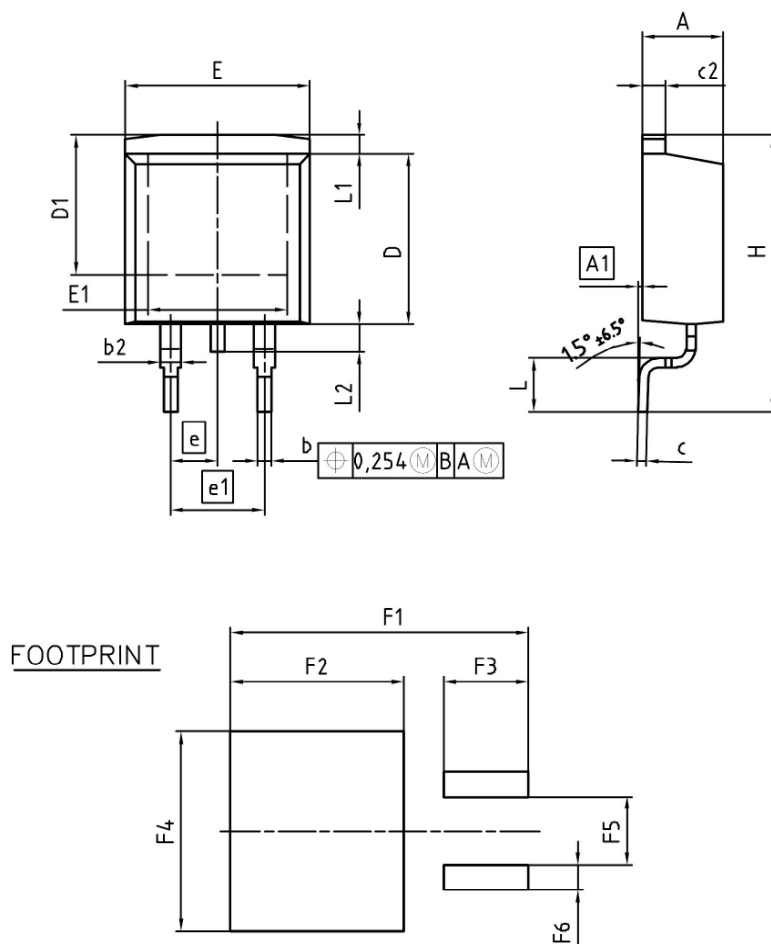
### Table 12 Unclamped inductive load

| Unclamped inductive load test circuit                                               | Unclamped inductive waveform                                                         |
|-------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------|
|  |  |

## 7 Package Outlines



**Figure 1 Outline PG-TO 247, dimensions in mm/inches**



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 4.30        | 4.57  | 0.169  | 0.180 |
| A1  | 0.00        | 0.25  | 0.000  | 0.010 |
| b   | 0.65        | 0.85  | 0.026  | 0.033 |
| b2  | 0.95        | 1.15  | 0.037  | 0.045 |
| c   | 0.33        | 0.65  | 0.013  | 0.026 |
| c2  | 1.17        | 1.40  | 0.046  | 0.055 |
| D   | 8.51        | 9.45  | 0.335  | 0.372 |
| D1  | 7.10        | 7.90  | 0.280  | 0.311 |
| E   | 9.80        | 10.31 | 0.386  | 0.406 |
| E1  | 6.50        | 8.60  | 0.256  | 0.339 |
| e   | 2.54        |       | 0.100  |       |
| e1  | 5.08        |       | 0.200  |       |
| N   | 2           |       | 2      |       |
| H   | 14.61       | 15.88 | 0.575  | 0.625 |
| L   | 2.29        | 3.00  | 0.090  | 0.118 |
| L1  | 0.70        | 1.60  | 0.028  | 0.063 |
| L2  | 1.00        | 1.78  | 0.039  | 0.070 |
| F1  | 16.05       | 16.25 | 0.632  | 0.640 |
| F2  | 9.30        | 9.50  | 0.366  | 0.374 |
| F3  | 4.50        | 4.70  | 0.177  | 0.185 |
| F4  | 10.70       | 10.90 | 0.421  | 0.429 |
| F5  | 3.65        | 3.85  | 0.144  | 0.152 |
| F6  | 1.25        | 1.45  | 0.049  | 0.057 |

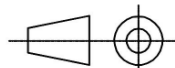
|                                                                                                              |
|--------------------------------------------------------------------------------------------------------------|
| DOCUMENT NO.<br>Z8B00003324                                                                                  |
| SCALE<br>0 5 7.5mm                                                                                           |
| EUROPEAN PROJECTION<br> |
| ISSUE DATE<br>30-08-2007                                                                                     |
| REVISION<br>01                                                                                               |

Figure 2 Outline PG-TO 263, dimensions in mm/inches

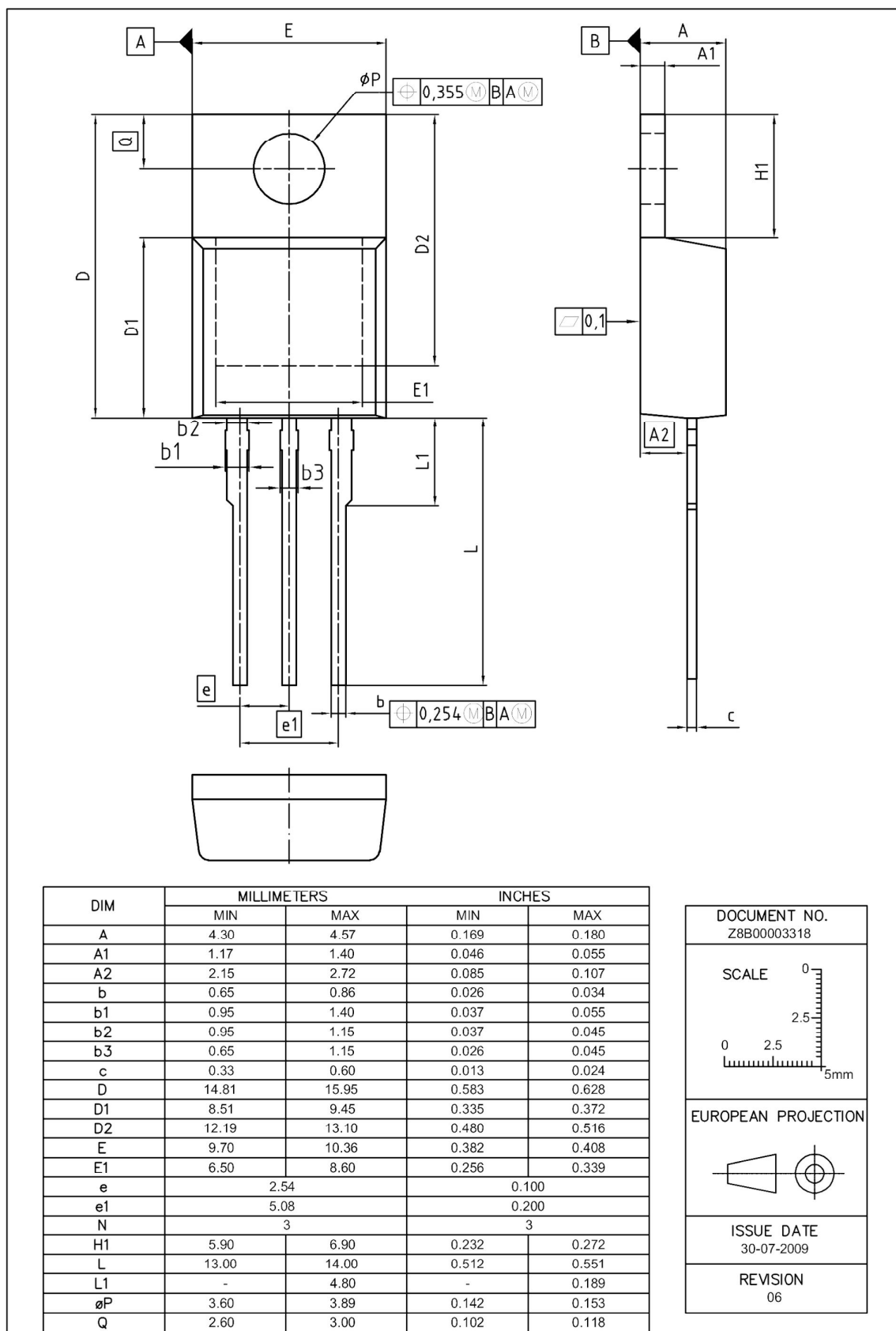
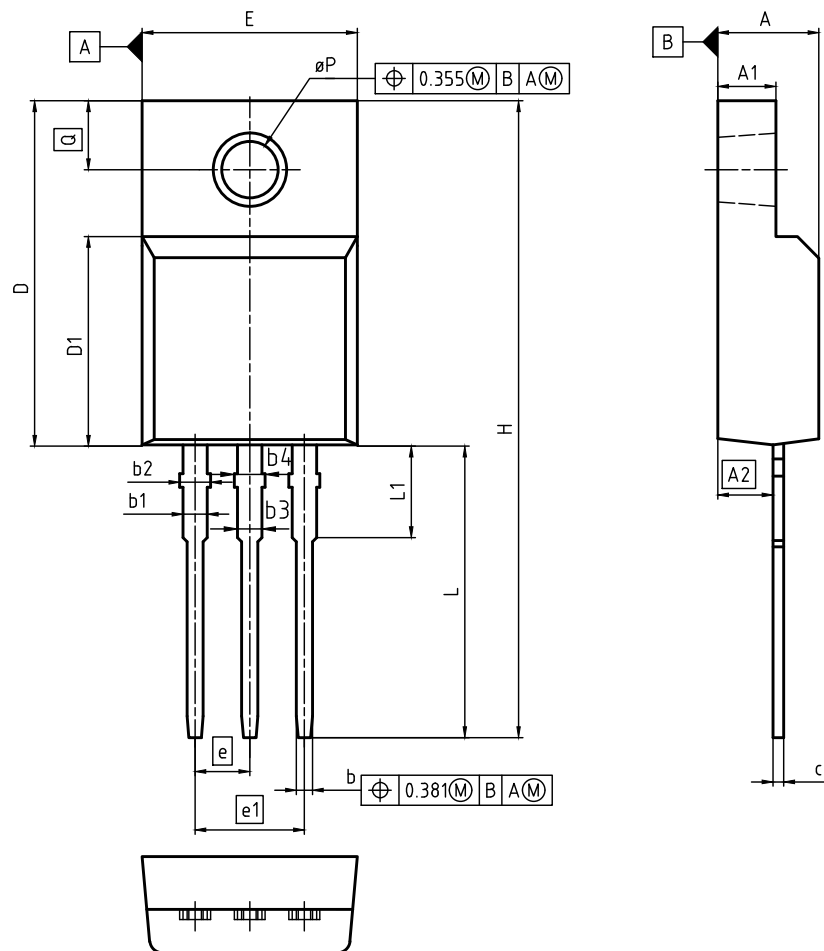
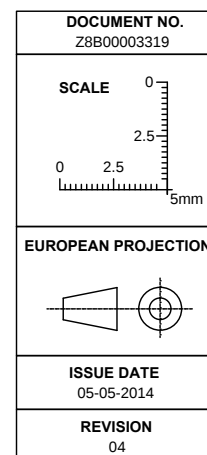


Figure 3 Outline PG-TO 220, dimensions in mm/inches



| DIM | MILLIMETERS |       | INCHES      |       |
|-----|-------------|-------|-------------|-------|
|     | MIN         | MAX   | MIN         | MAX   |
| A   | 4.50        | 4.90  | 0.177       | 0.193 |
| A1  | 2.34        | 2.85  | 0.092       | 0.112 |
| A2  | 2.42        | 2.86  | 0.095       | 0.113 |
| b   | 0.65        | 0.90  | 0.026       | 0.035 |
| b1  | 0.95        | 1.38  | 0.037       | 0.054 |
| b2  | 0.95        | 1.51  | 0.037       | 0.059 |
| b3  | 0.65        | 1.38  | 0.026       | 0.054 |
| b4  | 0.65        | 1.51  | 0.026       | 0.059 |
| c   | 0.40        | 0.63  | 0.016       | 0.025 |
| D   | 15.67       | 16.15 | 0.617       | 0.636 |
| D1  | 8.97        | 9.83  | 0.353       | 0.387 |
| E   | 10.00       | 10.65 | 0.394       | 0.419 |
| e   | 2.54 (BSC)  |       | 0.100 (BSC) |       |
| e1  | 5.08        |       | 0.200       |       |
| N   | 3           |       | 3           |       |
| H   | 28.70       | 29.75 | 1.130       | 1.171 |
| L   | 12.78       | 13.75 | 0.503       | 0.541 |
| L1  | 2.83        | 3.45  | 0.111       | 0.136 |
| øP  | 2.95        | 3.38  | 0.116       | 0.133 |
| Q   | 3.15        | 3.50  | 0.124       | 0.138 |



**Figure 4 Outline PG-TO 220 FullPAK, dimensions in mm/inches**

## 8 Appendix A

### Table 13 Related Links

- IFX CoolMOS™ P6 Webpage: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS™ P6 application note: [www.infineon.com](http://www.infineon.com)
- IFX CoolMOS™ P6 simulation model: [www.infineon.com](http://www.infineon.com)
- IFX Design tools: [www.infineon.com](http://www.infineon.com)

## Revision History

IPW60R330P6, IPB60R330P6, IPP60R330P6, IPA60R330P6

**Revision: 2015-07-10, Rev. 2.2**

Previous Revision

| Revision | Date       | Subjects (major changes since last revision) |
|----------|------------|----------------------------------------------|
| 2.0      | 2013-12-04 | Release of final version                     |
| 2.1      | 2013-12-05 | Release of multi-package datasheet           |
| 2.2      | 2015-07-10 | PG-TO 263 package added                      |

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